NSN 5961-00-912-5405

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View Online at https://aerobasegroup.com/nsn/5961-00-912-5405
Inclosure Material:
Metal
Overall Length:
Between 0.365 inches and 0.415 inches
Overall Diameter:
1.110 inches
Mounting Facility Quantity:
1
Internal Configuration:
Junction contact
Internal Junction Configuration:
Pnp
Mounting Method:
Threaded stud
Features Provided:
Hermetically sealed case
Thread Size:
0.250 inches
Semiconductor Material:
Germanium
Voltage Rating In Volts Per Characteristic:
50.0 breakdown voltage, collector-to-emitter, base open and 60.0 breakdown voltage, collector-to-emitter, with base short-circuited to
emitter and 80.0 collector to base voltage/static/emitter open and 28.0 emitter to base voltage, static, collector open
Current Rating Per Characteristic:
50.00 amperes source cutoff current
Power Rating Per Characteristic:
187.0 watts small-signal input power, common-collector
Maximum Operating Tempurature Per Measurement Point:
100.0 degrees celsius junction
Test Data Document:
81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification
format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain
environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).
Thread Series Designator:
Unf
Terminal Type And Quantity:
3 tab, solder lug
Specification Data:
81349-mil-s-19500/46 government specification
Shelf Life:
N/a
Unit Of Measure:

Nic

Demilitarization:

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